



浙江芯芯电子有限公司
ZHEJIANG XINXIN ELECTRICAL CO., LTD.

产品规格书

Specification of Products

产品名称：平板型

产品型号：KK2500A

浙江芯芯电子有限公司

ZHEJIANG XINXIN ELECTRICAL CO., LTD.

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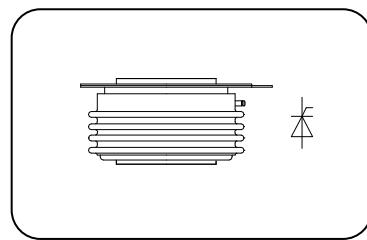
Features

- Interdigitated amplifying gates
- Fast turn-on and high dI/dt
- Low switching losses

Typical Applications

- Inductive heating
- Electronic welders
- Self-commutated inverters

$I_{T(AV)}$	2790A
V_{DRM}/V_{RRM}	1900~2500V
t_q	40~80μs
I_{TSM}	33.8 kA
I^2t	5712 10³A²S



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_j(^{\circ}C)$	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled, $T_c=55^{\circ}C$ $T_c=85^{\circ}C$ old model	125			2790	A
						1850	
						2500	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	$V_{DRM} \& V_{RRM}$, tp=10ms $V_{DSM} \& V_{RSM} = V_{DRM} \& V_{RRM} + 100V$	125	1900		2500	V
I_{DRM} I_{RRM}	Repetitive peak current	$V_D = V_{DRM}$ $V_R = V_{RRM}$	125			200	mA
I_{TSM}	Surge on-state current	10ms half sine wave $V_R=0.6V_{RRM}$	125			33.8	kA
I^2t	I^2t for fusing coordination					5712	$A^2s * 10^3$
V_{TO}	Threshold voltage		125			1.48	V
r_T	On-state slop resistance					0.15	mΩ
V_{TM}	Peak on-state voltage	$I_{TM}=4000A$, F=40kN	125			2.08	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			500	V/μs
di/dt	Critical rate of rise of on-state current	$V_{DM}=67\%V_{DRM}$, to 3000A Gate pulse $t_r \leq 0.5\mu s$ $I_{GM}=1.5A$	125			1200	A/μs
Q_{rr}	Recovery charge	$I_{TM}=2000A$, tp=2000μs, $di/dt=-60A/\mu s$, $V_R=50V$	125		1460		μC
t_q	Circuit commutated turn-off time	$I_{TM}=2000A$, tp=1000μs, $V_R=50V$ $dv/dt=30V/\mu s$, $di/dt=-20A/\mu s$	125	40		80	μs
I_{GT}	Gate trigger current	$V_A=12V$, $I_A=1A$	25	40		450	mA
V_{GT}	Gate trigger voltage			0.9		4.5	V
I_H	Holding current			20		1000	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125	0.3			V
$R_{th(j-c)}$	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 40kN				0.010	°C /W
	Thermal resistance case to heat sink					0.003	
F_m	Mounting force			35		47	kN
T_{stg}	Stored temperature			-40		140	°C
W_t	Weight				1100		g
Outline		KT73ct					

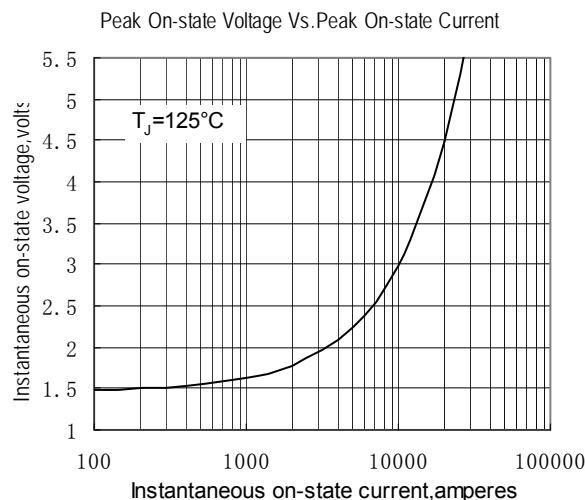


Fig.1

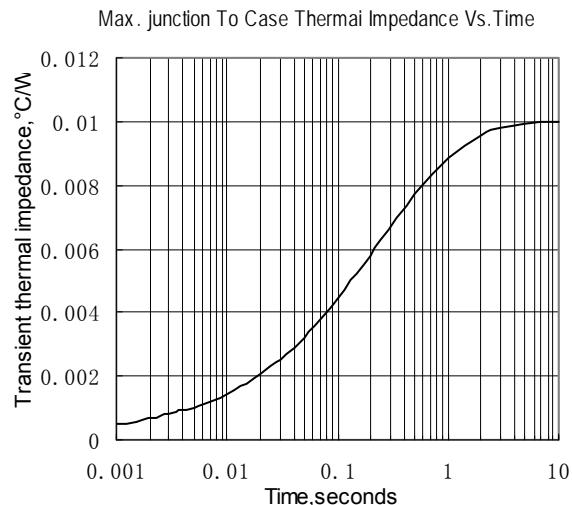


Fig.2

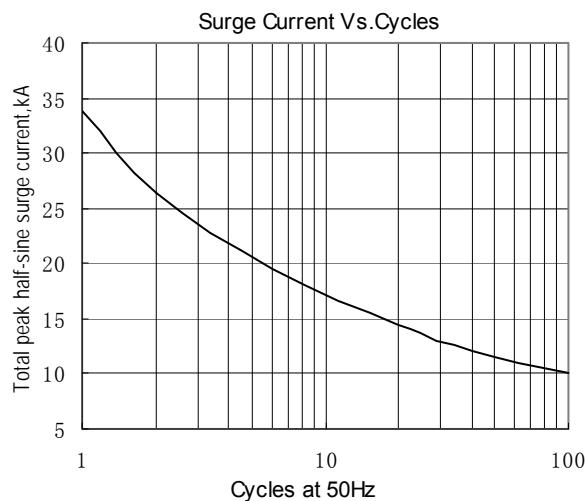


Fig.3

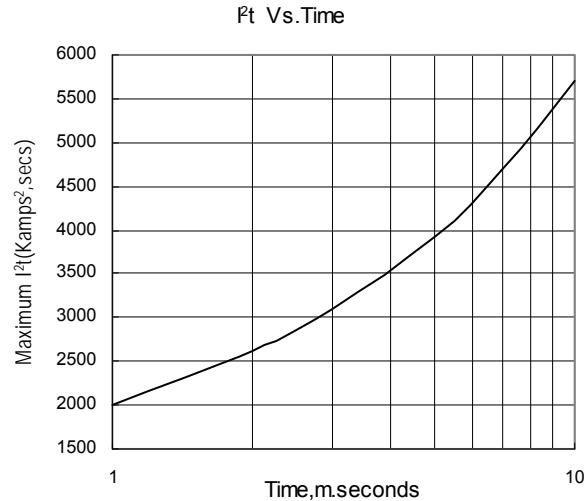


Fig.4

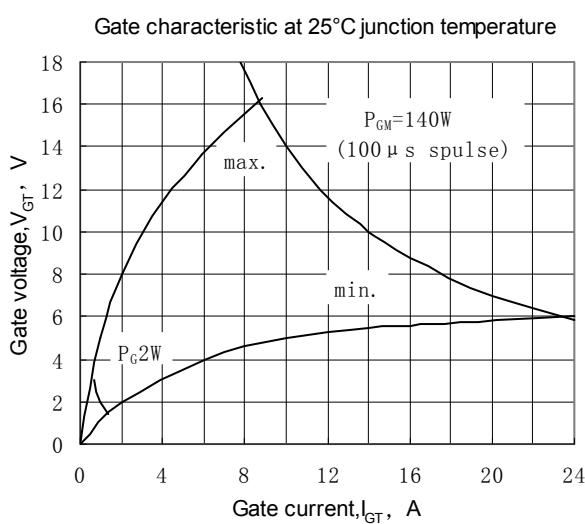


Fig.5

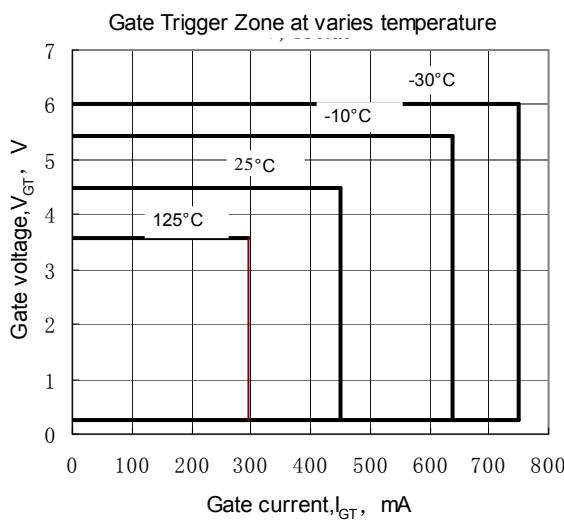


Fig.6

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Outline:

